

Docket No. 242452US2/shb

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yukio TANIGUCHI, et al.

SERIAL NO: 10/656,202

GAU:

FILED: September 8, 2003

EXAMINER:

FOR: CRYSTALLIZATION APPARATUS, CRYSTALLIZATION METHOD, AND PHASE SHIFTER



INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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DOCKET NO.: 242452US2/shb



Page 1 of 1

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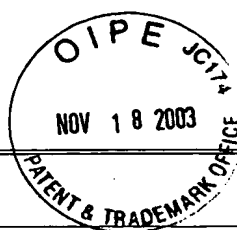
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STATEMENT OF RELEVANCY

References AU and AV on Form 1449 are discussed in the specification.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

242452US2

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LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Yukio TANIGUCHI, et al.

FILING DATE

September 8, 2003

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	6-289431	10/18/1994	JAPAN (with partial English translation)		X
	AP	2000-82669	03/21/2000	JAPAN (with English Abstract)		X
	AQ					
	AR					
	AS					
	AT					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AU	M. MATSUMURA, Applied Surface Science, vol. 21, no. 5, pages 278-287, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", 2000 (with partial English translation)	
	AV	C.-H. OH, et al., Applied Surface Science 154-155, pages 105-111, "OPTIMIZATION OF PHASE-MODULATED EXCIMER-LASER ANNEALING METHOD FOR GROWING HIGHLY-PACKED LARGE-GRAINS IN Si THIN-FILMS", 2000	
	AW	M. MATSUMURA, Physica Status Solidi (a), vol. 166, no. 2, pages 715-728, "APPLICATION OF EXCIMER-LASER ANNEALING TO AMORPHOUS, POLY-CRYSTAL AND SINGLE-CRYSTAL SILICON THIN-FILM TRANSISTORS", 1998	
	AX	M. MATSUMURA, et al., Thin Solid Films, vol. 337, pages 123-128, "ADVANCED EXCIMER-LASER ANNEALING PROCESS FOR QUASI SINGLE-CRYSTAL SILICON THIN-FILM DEVICES", 1999	
	AY	C.-H. OH, et al., Japanese Journal of Applied Physics, vol. 37, no. 10, pages 5474-5479, "PREPARATION OF POSITION-CONTROLLED CRYSTAL-SILICON ISLAND ARRAYS BY MEANS OF EXCIMER-LASER ANNEALING", 1998	
	AZ	K. INOUE, et al., The Transactions of the Institute of Electronics, Information and Communication Engineers C, vol. J85-C, no. 8, pages 624-629, "AMPLITUDE AND PHASE MODULATED EXCIMER-LASER MELT-REGROWTH METHOD OF SILICON THIN-FILMS- A NEW GROWTH METHOD OF 2-D POSITION-CONTROLLED LARGE-GRAINS", 2002 (with partial English translation)	<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.